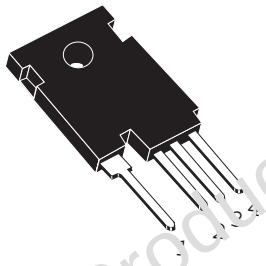
STC08IE120HV

Emitter Switched Bipolar Transistor
ESBT® 1200 V - 8 A - 0.10 Ω

General features

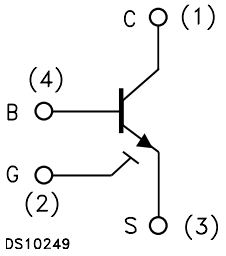
$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
0.8 V	8 A	0.10 Ω

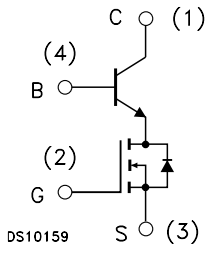
- High voltage / high current Cascode configuration
- Low equivalent on resistance
- very fast-switch up to 150 kHz
- Squared RBSOA up to 1200V
- Very low C_{iss} driven by R_G = 47Ω
- Very low turn-off cross over time



TO247-4L HV

Internal schematic diagrams





Applications

- Flyback / forward SMPS
- Sepic PFC

Description

The STC08IE120HV is manufactured in Monolithic ESBT Technology, aimed to provide best performances in high frequency / high voltage applications.

It is designed for use in Gate Driven based topologies.

Order codes

Part Number	Marking	Package	Packaging
STC08IE120HV	C08IE120HV	TO247-4L HV	Tube

Contents

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage (V_{BS} = V_{GS} = 0 V)	1200	V
$V_{BS(OS)}$	Base-source voltage (I_C = 0, V_{GS} = 0 V)	30	V
$V_{SB(OS)}$	Source-base voltage (I_C = 0, V_{GS} = 0 V)	17	V
V_{GS}	Gate-source voltage	± 17	V
I_C	Collector current	8	A
I_{CM}	Collector peak current (t_P < 5ms)	24	A
I_B	Base current	6	A
I_{BM}	Base peak current (t_P < 5ms)	12	A
P_{tot}	Total dissipation at T_c = 25°C	208	W
T_{stg}	Storage temperature	-40 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter		Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	max	0.6	°C/W

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CS(SS)}$	Collector-source current (V_{BS} = V_{GS} = 0)	V_{CE} = 1200V			100	µA
$I_{BS(OS)}$	Base-source current (I_C = 0, V_{GS} = 0)	$V_{BS(OS)}$ = 30V			10	µA
$I_{SB(OS)}$	Source-base current (I_C = 0, V_{GS} = 0)	$V_{SB(OS)}$ = 17V			100	µA
$I_{GS(OS)}$	Gate-source leakage	V_{GS} = ± 17V			100	nA
$V_{CS(ON)}$	Collector-source ON voltage	V_{GS} = 10V I_C = 8A I_B = 1.6A V_{GS} = 10V I_C = 4A I_B = 0.4A		0.8 0.5	1 1.2	V V
h_{FE}	DC current gain	V_{GS} = 10V I_C = 8A V_{CS} = 1V V_{GS} = 10V I_C = 4A V_{CS} = 1V	5 7			
$V_{BS(ON)}$	Base Source ON voltage	V_{GS} = 10V I_C = 8A I_B = 1.6A V_{GS} = 10V I_C = 4A I_B = 0.4A		1.5 1.5		V V
$V_{GS(th)}$	Gate threshold voltage	V_{BS} = V_{GS} I_B = 250µA	2	3	4	V
C_{ISS}	Input capacitance	V_{CS} = 25V f = 1MHz V_{GS} = 0		550		pF
$Q_{GS(tot)}$	Gate-source charge	V_{GS} = 10V		26		nC
t_s t_f	INDUCTIVE LOAD Storage time Fall time	I_C = 4A I_B = 0.8A V_{GS} = 10V V_{Clamp} = 960V R_G = 47Ω t_p = 4µs		670 15		ns ns
t_s t_f	INDUCTIVE LOAD Storage time Fall time	I_C = 4A I_B = 0.4A V_{GS} = 10V V_{Clamp} = 960V R_G = 47Ω t_p = 4µs		340 10.2		ns ns
V_{CSW}	Maximum collector-source voltage switched without snubber	R_G = 47Ω h_{FE} = 5A I_C = 8A	1200			V
$V_{CS(dyn)}$	Collector-source dynamic voltage (500ns)	V_{CC} = V_{Clamp} = 400V V_{GS} = 10V R_G = 47Ω I_C = 4A I_B = 0.8A I_{Bpeak} = 4A t_{peak} = 500ns		5.75		V
$V_{CS(dyn)}$	Collector-source dynamic voltage (1 µs)	V_{CC} = V_{Clamp} = 400V V_{GS} = 10V R_G = 47Ω I_C = 4A I_B = 0.8A I_{Bpeak} = 4A t_{peak} = 500ns		3.35		V

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

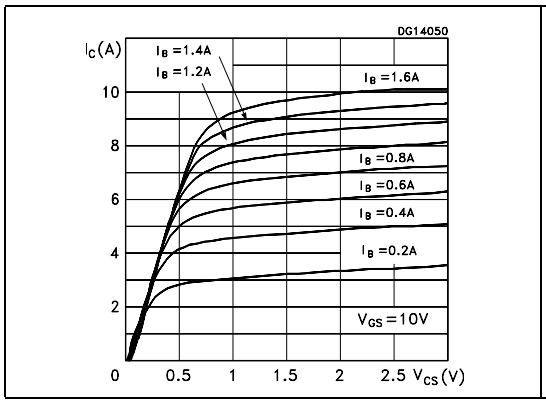


Figure 2. DC current gain

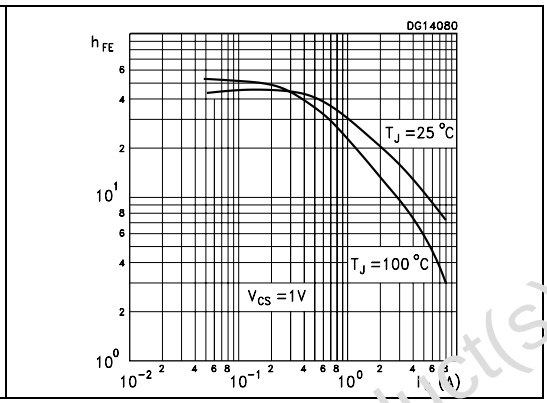


Figure 3. Collector-source On voltage

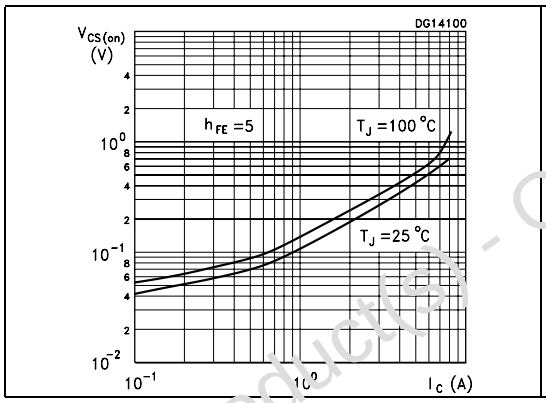


Figure 4. Collector-source On voltage

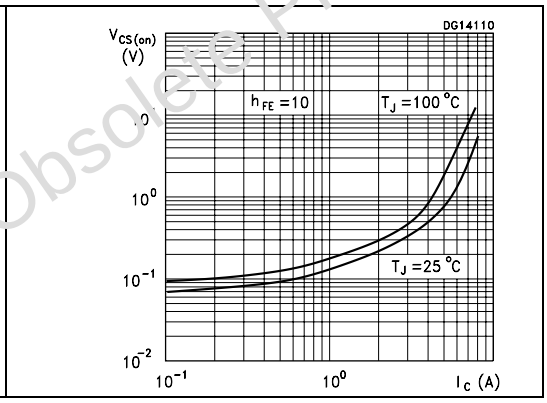


Figure 5. Base-source On voltage

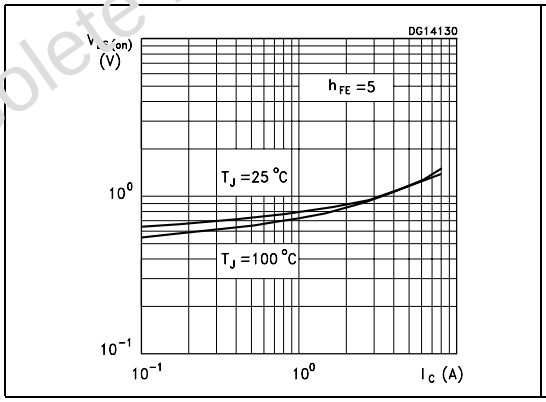


Figure 6. Base-source On voltage

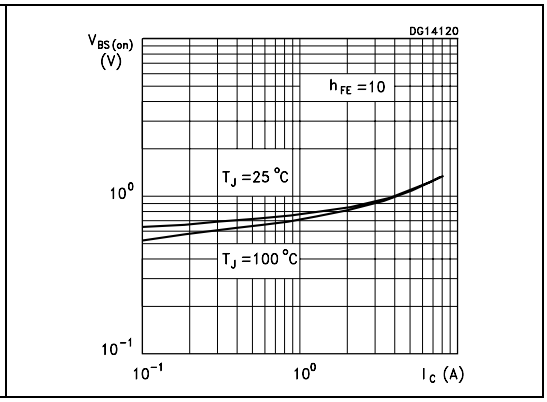


Figure 7. Reverse biased safe operting area

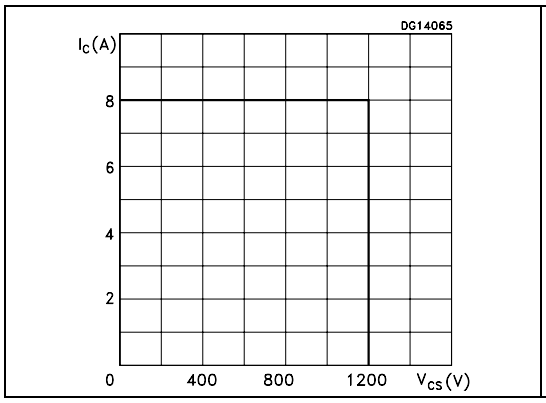


Figure 8. Gate threshold voltage vs temperature

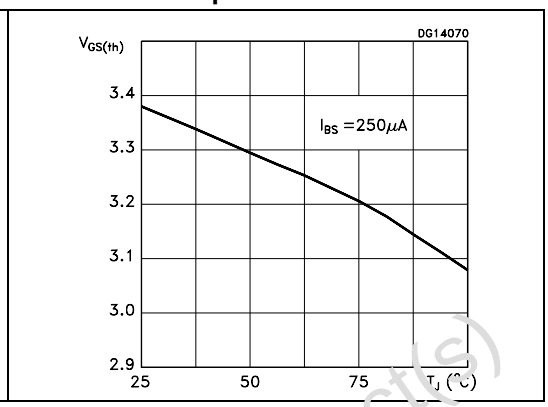


Figure 9. Dynamic collector-emitter saturation voltage

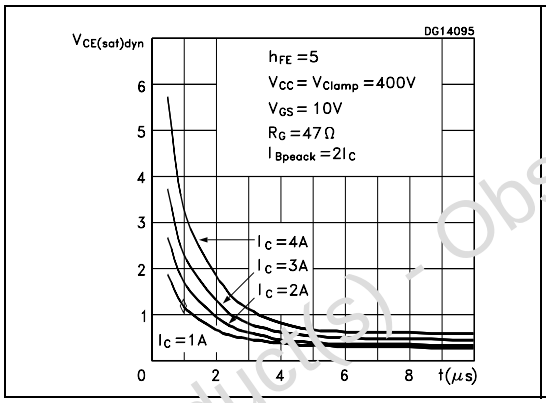


Figure 10. Inductive load switching time

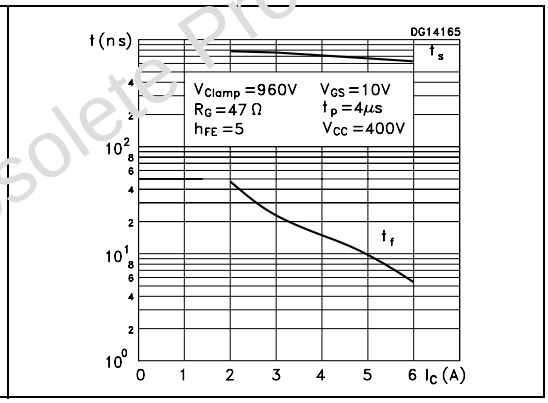
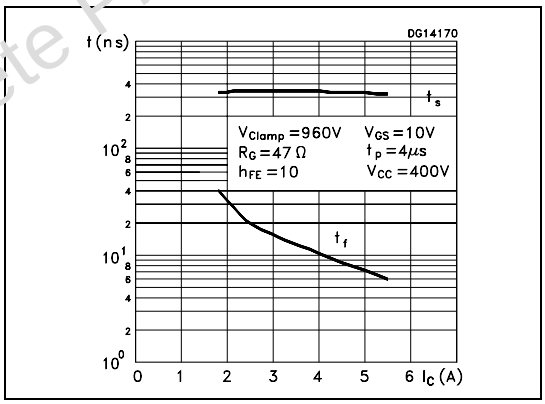
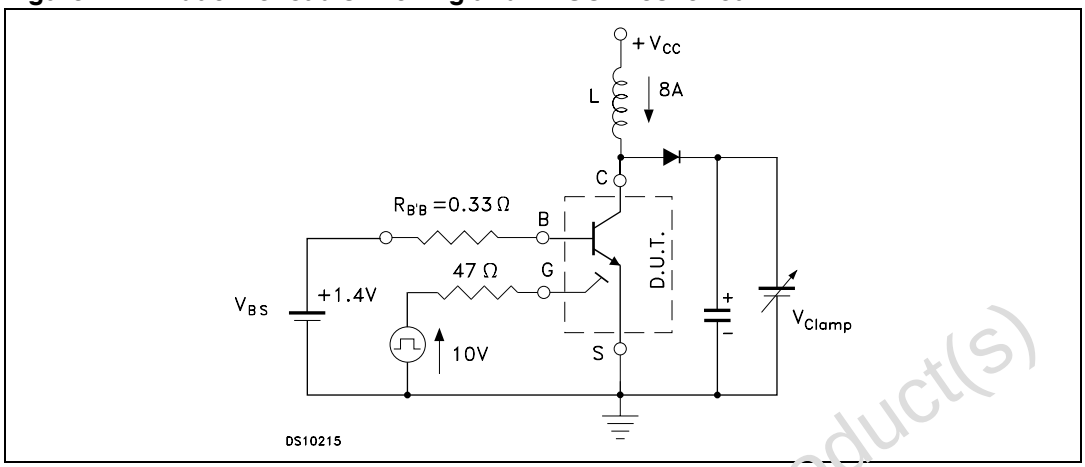


Figure 11. Inductive load switching time



2.2 Test circuits

Figure 12. Inductive load switching and RBSOA test circuit

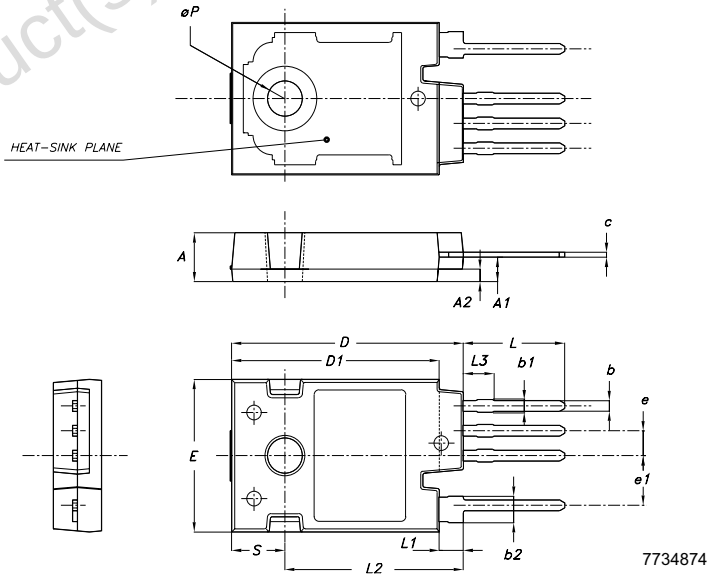


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO247-4LHV MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e	2.54		
e1	5.08		
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
∅P	3.55		3.65
S		5.50	



4 Revision history

Table 4. Revision history

Date	Revision	Changes
11-May-2006	1	Initial release.
16-Oct-2006	2	The lower temperature storage limit has been modified on page 3.
12-Jan-2007	3	The device's commercial code has been changed from preliminary to full.

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